

NCE N-Channel Super Trench Power MOSFET

Description

The series of devices uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

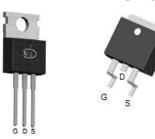
General Features

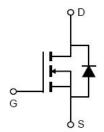
- V_{DS} =200V, I_D =70A $R_{DS(ON)}$ =16.5m Ω , typical @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

TO-220-3L

TO-263-2L





Schematic Diagram

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|-----------|----------------|-----------|------------|-----------|
| NCEP0260 | NCEP0260 | TO-220-3L | - | - | - |
| NCEP0260D | NCEP0260D | TO-263-2L | Ø330mm | 24mm | 800 units |

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|-----------------------|------------|------------|
| Drain-Source Voltage | Vos | 200 | V |
| Gate-Source Voltage | Vgs | ±20 | V |
| Drain Current-Continuous | I _D | 70 | А |
| Drain Current-Continuous(T _C =100 ℃) | I _D (100℃) | 49 | А |
| Pulsed Drain Current | I _{DM} | 280 | Α |
| Maximum Power Dissipation | P _D | 285 | W |
| Derating factor | | 1.9 | W/℃ |
| Single pulse avalanche energy (Note 1) | Eas | 135 | mJ |
| Operating Junction and Storage Temperature Range | T_{J} , T_{STG} | -55 To 175 | $^{\circ}$ |

Thermal Characteristic

| Thermal Resistance, Junction-to-Case | ReJC | 0.53 | °C/W |
|--------------------------------------|------|------|------|

NCEP0260,NCEP0260D

Electrical Characteristics (T_C=25°C unless otherwise noted)

| BV _{DSS} I _{DSS} I _{GSS} | V _{GS} =0V I _D =250µA V _{DS} =200V,V _{GS} =0V | 200 | | | |
|---|--|---|---|---|---|
| I _{DSS} | · | 200 | | | |
| | V _{DS} =200V,V _{GS} =0V | | - | - | V |
| I _{GSS} | | - | - | 1 | μΑ |
| | V _{GS} =±20V,V _{DS} =0V | - | - | ±100 | nA |
| | | | | | |
| $V_{GS(th)}$ | $V_{DS}=V_{GS}$, $I_{D}=250\mu A$ | 2.0 | 3.0 | 4.0 | V |
| R _{DS(ON)} | V _{GS} =10V, I _D =30A | - | 16.5 | 23 | mΩ |
| g FS | V _{DS} =5V,I _D =30A | - | 50 | - | S |
| | | | | | |
| C _{lss} | V 400VVV 0V | - | 3300 | - | PF |
| Coss | , , , | - | 255 | - | PF |
| C _{rss} | F=1.UIVIHZ | - | 20 | - | PF |
| | | | | | |
| t _{d(on)} | | - | 25 | - | nS |
| t _r | V_{DD} =100 V , I_D =30 A | - | 21 | - | nS |
| t _{d(off)} | V_{GS} =10 V , R_{G} =4.7 Ω | - | 56 | - | nS |
| tf | | - | 15 | - | nS |
| Qg | V 400V/I 20A | - | 50 | | nC |
| Q _{gs} | • | - | 15.2 | | nC |
| Q _{gd} | V _{GS} -10V | - | 14.5 | | nC |
| , | | | | | |
| V _{SD} | V_{GS} =0 V , I_{S} =30 A | - | | 1.2 | V |
| Is | | - | - | 65 | Α |
| t _{rr} | T _J = 25°C, I _F = 30A | - | 140 | | nS |
| Qrr | di/dt = 100A/μs | - | 460 | | nC |
| | RDS(ON) gFS Clss Coss Crss td(on) tr dd(off) tf Qg Qgs Qgd VSD Is trr | $\begin{array}{c ccccccccccccccccccccccccccccccccccc$ | $\begin{array}{c ccccccccccccccccccccccccccccccccccc$ | $\begin{array}{c ccccccccccccccccccccccccccccccccccc$ | $\begin{array}{c ccccccccccccccccccccccccccccccccccc$ |

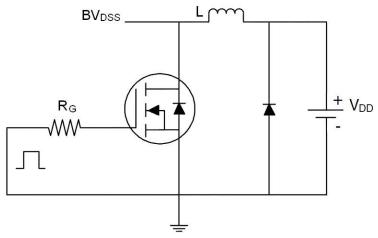
Notes:

- 1. EAS condition : Tj=25 $^{\circ}$ C,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

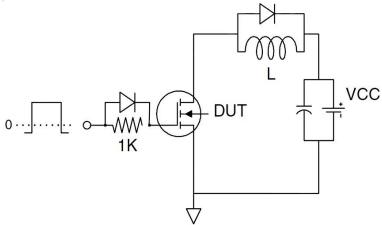


Test Circuit

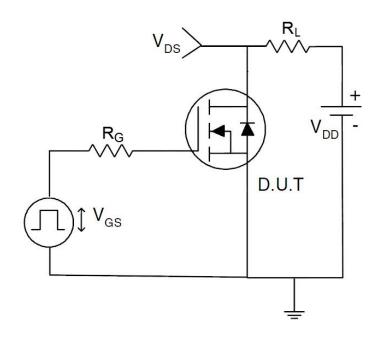
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

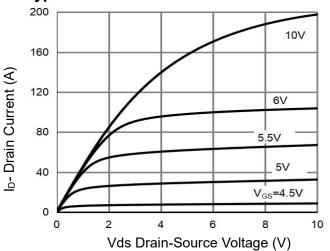


Figure 1 Output Characteristics

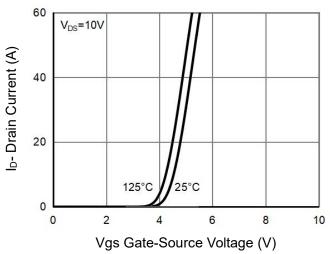


Figure 2 Transfer Characteristics

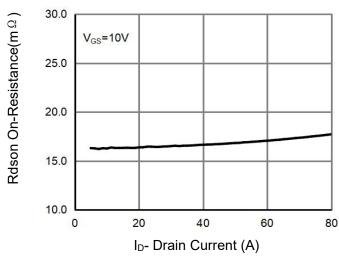


Figure 3 Rdson- Drain Current

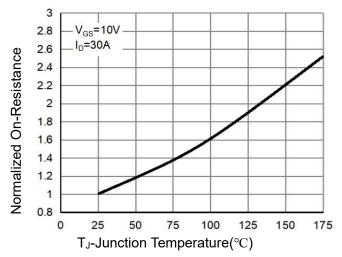


Figure 4 Rdson-JunctionTemperature

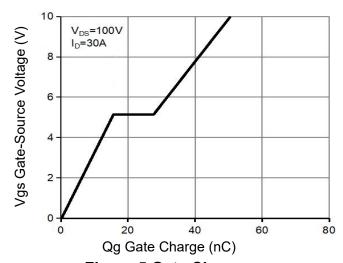


Figure 5 Gate Charge

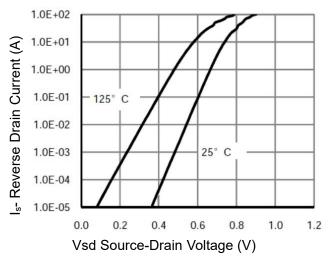


Figure 6 Source- Drain Diode Forward



C Capacitance (pF)

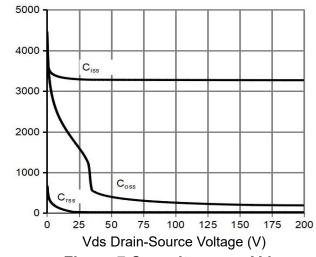


Figure 7 Capacitance vs Vds

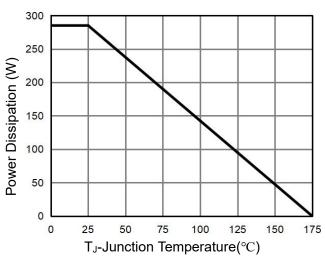


Figure 9 Power De-rating

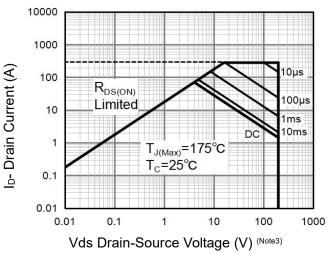


Figure 8 Safe Operation Area

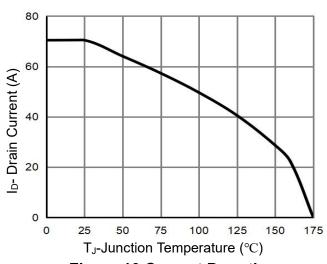
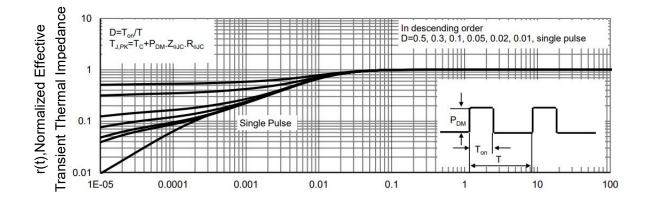


Figure 10 Current De-rating

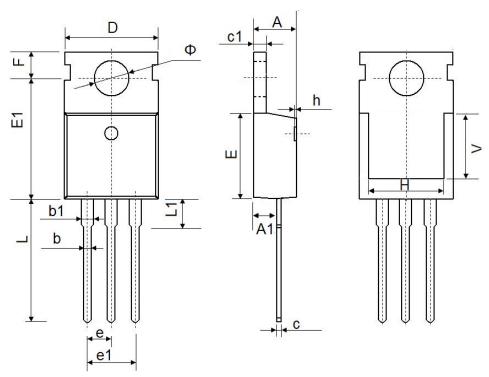


Square Wave Pluse Duration(sec)

Figure 12 Normalized Maximum Transient Thermal Impedance



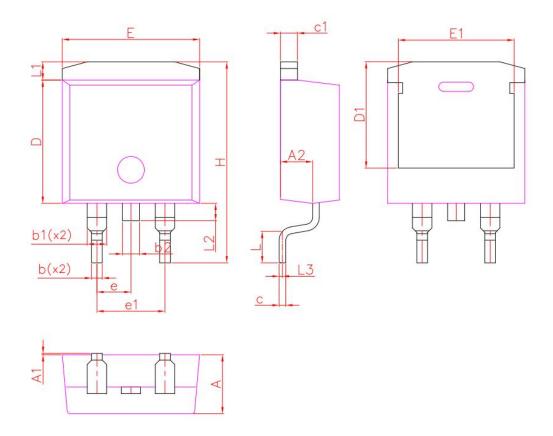
TO-220-3L Package Information



| O | Dimensions | In Millimeters | Dimensions In Inches | | | |
|--------|------------|----------------|----------------------|------------|--|--|
| Symbol | Min. | Max. | Min. | Max. | | |
| А | 4.400 | 4.600 | 0.173 | 0.181 | | |
| A1 | 2.250 | 2.550 | 0.089 | 0.100 | | |
| b | 0.710 | 0.910 | 0.028 | 0.036 | | |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 | | |
| С | 0.330 | 0.650 | 0.013 | 0.026 | | |
| c1 | 1.200 | 1.400 | 0.047 | 0.055 | | |
| D | 9.910 | 10.250 | 0.390 | 0.404 | | |
| E | 8.9500 | 9.750 | 0.352 | 0.384 | | |
| E1 | 12.650 | 12.950 | 0.498 | 0.510 | | |
| е | 2.540 | 2.540 TYP. | | 0.100 TYP. | | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 | | |
| F | 2.650 | 2.950 | 0.104 | 0.116 | | |
| Н | 7.900 | 8.100 | 0.311 | 0.319 | | |
| h | 0.000 | 0.300 | 0.000 | 0.012 | | |
| L | 12.900 | 13.400 | 0.508 | 0.528 | | |
| L1 | 2.850 | 3.250 | 0.112 | 0.128 | | |
| V | 6.900 | 6.900 REF. | | 0.276 REF. | | |
| Ф | 3.400 | 3.800 | 0.134 | 0.150 | | |



TO-263-2L Package Information



| | TO263 | | | | | |
|-------------------------------|------------------|-------|-------|--|--|--|
| DIM. | MIN. | NOM. | MAX. | | | |
| А | 4.20 | 4.40 | 4.60 | | | |
| A1 | 0.00 | 0.10 | 0.25 | | | |
| A2 | 2.20 | 2.40 | 2.60 | | | |
| b | 0.70 | 0.80 | 0.90 | | | |
| b1 | 1.20 | 1.45 | 1.75 | | | |
| b2 | 1.17 | 1.27 | 1.37 | | | |
| С | 0.40 | 0.50 | 0.60 | | | |
| c1 | 1.15 | 1.27 | 1.40 | | | |
| D | 9.10 | 9.20 | 9.30 | | | |
| D1 | 7.63 | 7.93 | 8.23 | | | |
| E | 10.05 10.25 10.4 | | 10.45 | | | |
| E1 | 8.35 | 8.65 | 8.95 | | | |
| е | 2.54BSC | | | | | |
| e1 | 5.08BSC | | | | | |
| Н | 14.61 | 15.00 | 15.88 | | | |
| L | 1.78 | 2.35 | 2.79 | | | |
| L1 | 1.36REF | | | | | |
| L2 | 1.3REF | | | | | |
| L3 | 0.25REF | | | | | |
| All dimensions in millimeters | | | | | | |

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NCEP0260, NCEP0260D

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